

CLAIMS

1. A high frequency circuit characterized by comprising:

5 a plurality of shunt paths including active elements and
impedance elements in between a high frequency transmission
path and a ground;

wherein said plurality of shunt circuits form a parallel
resonance circuit of said impedance elements when each of said
active elements is ON, and a serial resonance circuit of said
10 impedance elements when each of said active elements is OFF.

2. The high frequency circuit according to claim 1
characterized in that:

15 said active element is a field effect transistor.

3. The high frequency circuit according to claim 2
characterized in that:

20 said field effect transistor is made of gallium arsenic
series material.

4. The high frequency circuit according to claim 1
characterized in that:

25 said plurality of shunt paths are formed on a same
substrate.

5. The high frequency circuit according to claim 1
characterized in that:

an inductor forming said plurality of shunt paths is
replaced with inductance components of an IC bonding wire.